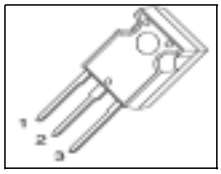
Cool MOS™ Power Transistor

V_{DS} @ T_{jmax}	650	V
$R_{DS(on)}$	0.28	Ω
I_D	15	A

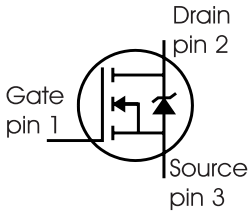
Feature

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme d*v*/d*t* rated
- Ultra low effective capacitances
- Improved transconductance
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC[0)] for target applications

PG-TO247



Type	Package	Ordering Code	Marking
SPW15N60C3	PG-TO247	Q67040-S4604	15N60C3



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current T_C = 25 °C T_C = 100 °C	I_D	 15 9.4	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\ puls}$	45	
Avalanche energy, single pulse I_D = 7.5 A, V_{DD} = 50 V	E_{AS}	460	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax}[1] I_D = 15 A, V_{DD} = 50 V	E_{AR}	0.8	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	15	A
Reverse diode d*v*/d*t* [4)]	d*v*/d*t*	15	V/ns
Gate source voltage static	V_{GS}	±20	V
Gate source voltage AC (f >1Hz)	V_{GS}	±30	
Power dissipation, T_C = 25°C	P_{tot}	156	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope V_{DS} = 480 V, I_D = 15 A, T_j = 125 °C	dv/dt	50	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	0.8	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at T_j=25°C unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=0.25mA	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	V_{GS}=0V, I_D=15A	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	I_D=675µA, V_{GS}=V_{DS}	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	V_{DS}=600V, V_{GS}=0V, T_j=25°C, T_j=150°C	 - -	 0.1 -	 1 100	µA
Gate-source leakage current	I_{GSS}	V_{GS}=30V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=9.4A, T_j=25°C T_j=150°C	 - -	 0.25 0.68	 0.28 -	Ω
Gate input resistance	R_G	f=1MHz, open Drain	-	1.23	-	

Electrical Characteristics , at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	V_{DS}≥2*I_D*$R_{DS(on)max}$, I_D=9.4A	-	11.9	-	S
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	1660	-	pF
Output capacitance	C_{oss}		-	540	-	
Reverse transfer capacitance	C_{rss}		-	40	-	
Effective output capacitance,[2] energy related	$C_{o(er)}$	V_{GS}=0V, V_{DS}=0V to 480V	-	80	-	pF
Effective output capacitance,[3] time related	$C_{o(tr)}$		-	127	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=380V, V_{GS}=0/10V, I_D=15A, R_G=4.3Ω	-	10	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	50	80	
Fall time	t_f		-	5	10	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	V_{DD}=480V, I_D=15A	-	7	-	nC
Gate to drain charge	Q_{gd}		-	29	-	
Gate charge total	Q_g	V_{DD}=480V, I_D=15A, V_{GS}=0 to 10V	-	63	-	
Gate plateau voltage	$V_{(plateau)}$	V_{DD}=480V, I_D=15A	-	5	-	V

[0] J-STD20 and JESD22

[1] Repetitve avalanche causes additional power losses that can be calculated as P_{AV}=E_{AR}*f.

[2] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

[3] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

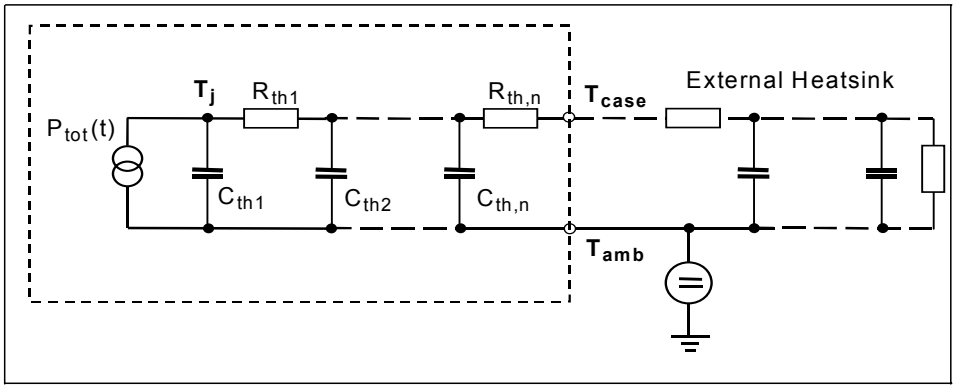
[4] I_{SD}<=I_D, di/dt<=400A/us, V_{DClink}=400V, V_{peak}<$V_{BR, DSS}$, T_j<$T_{j,max}$.
Identical low-side and high-side switch.

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	T_C=25°C	-	-	15	A
Inverse diode direct current, pulsed	I_{SM}		-	-	45	
Inverse diode forward voltage	V_{SD}	V_{GS}=0V, I_F=I_S	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=480V, I_F=I_S ,	-	460	-	ns
Reverse recovery charge	Q_{rr}	di_F/dt=100A/µs	-	27	-	µC
Peak reverse recovery current	I_{rrm}		-	55	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	tbd	-	A/µs

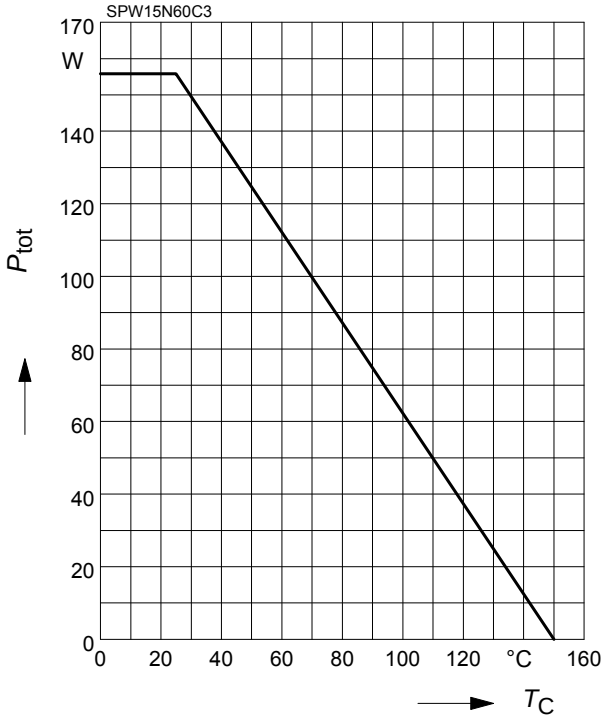
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.012	K/W	C_{th1}	0.0002495	Ws/K
R_{th2}	0.023		C_{th2}	0.0009406	
R_{th3}	0.043		C_{th3}	0.001298	
R_{th4}	0.156		C_{th4}	0.00362	
R_{th5}	0.178		C_{th5}	0.009046	
R_{th6}	0.072		C_{th6}	0.412	



1 Power dissipation

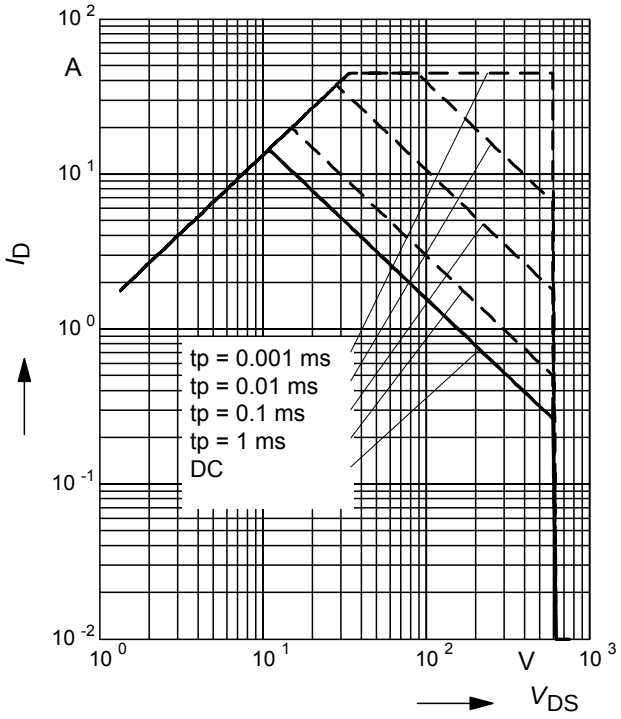
$P_{tot} = f(T_C)$



2 Safe operating area

$I_D = f(V_{DS})$

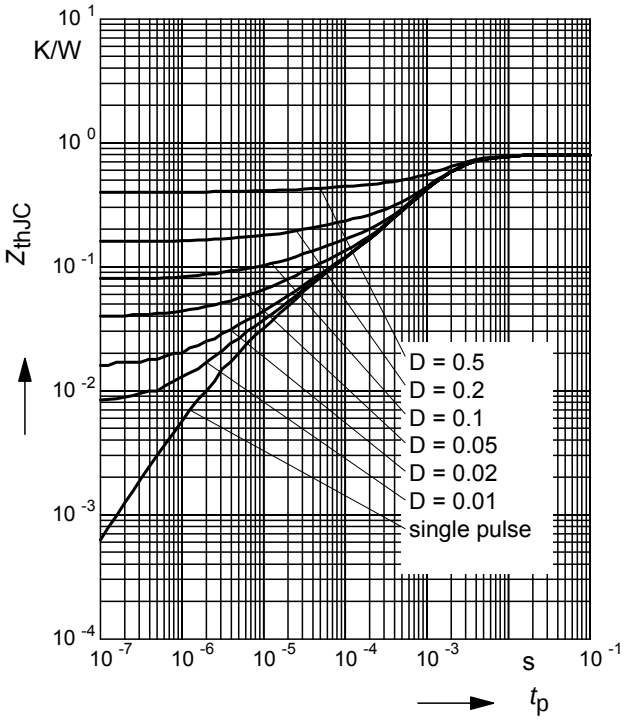
parameter : $D = 0$, T_C=25°C



3 Transient thermal impedance

$Z_{thJC} = f(t_p)$

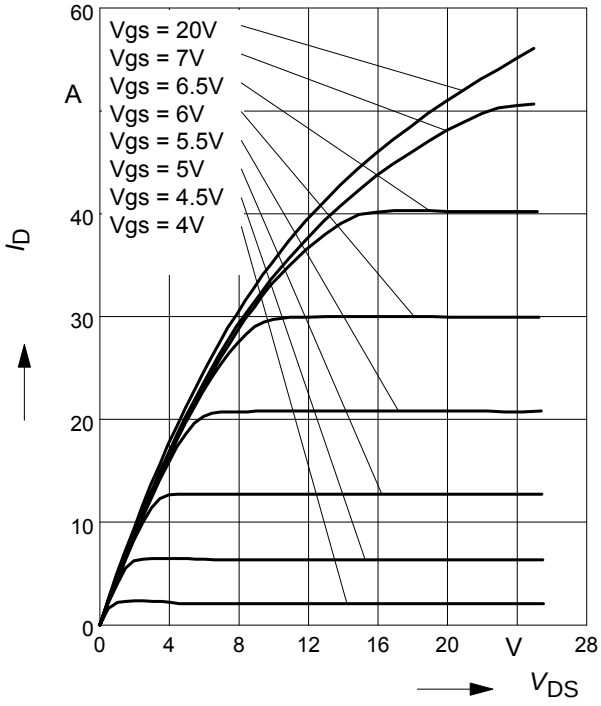
parameter: $D = t_p/T$



4 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=25°C

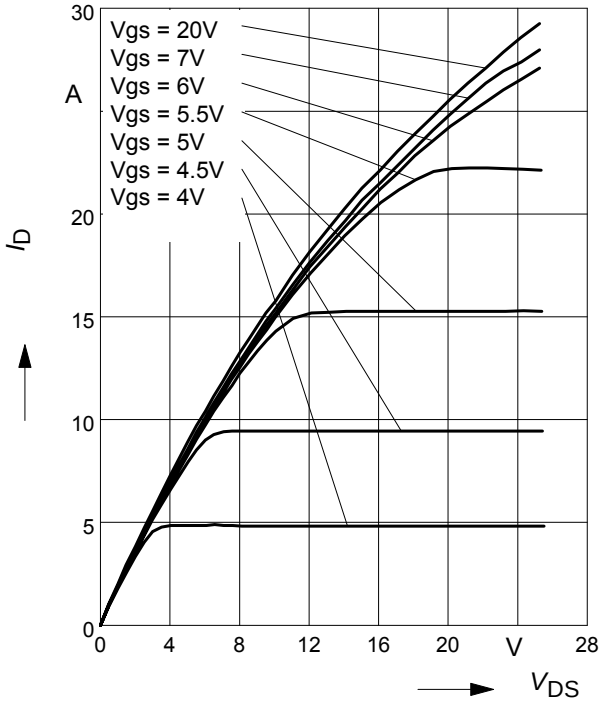
parameter: t_p = 10 µs, V_{GS}



5 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=150°C

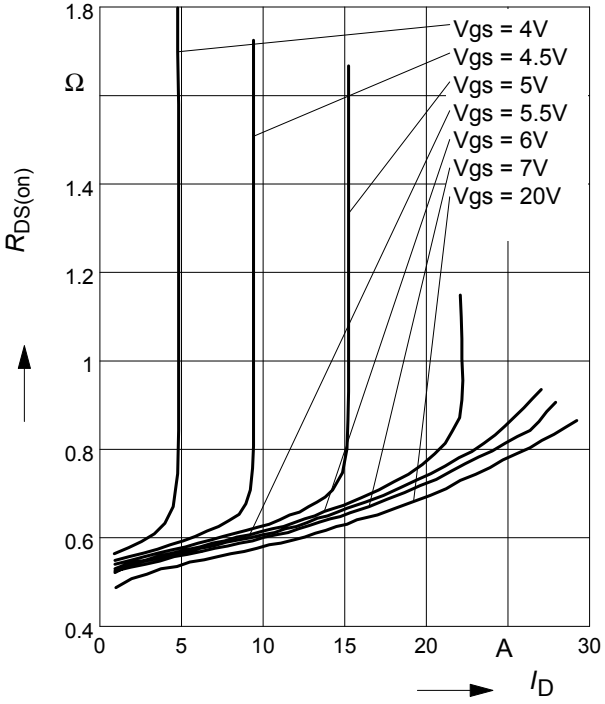
parameter: t_p = 10 µs, V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$

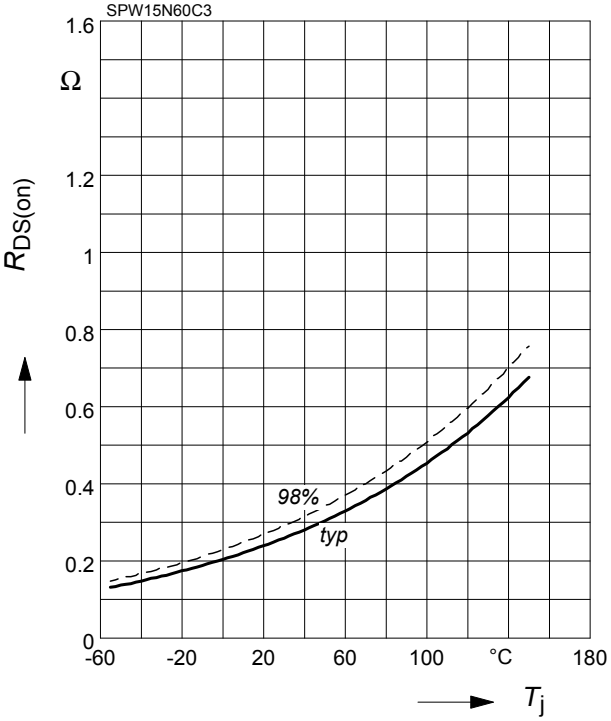
parameter: T_j=150°C, V_{GS}



7 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

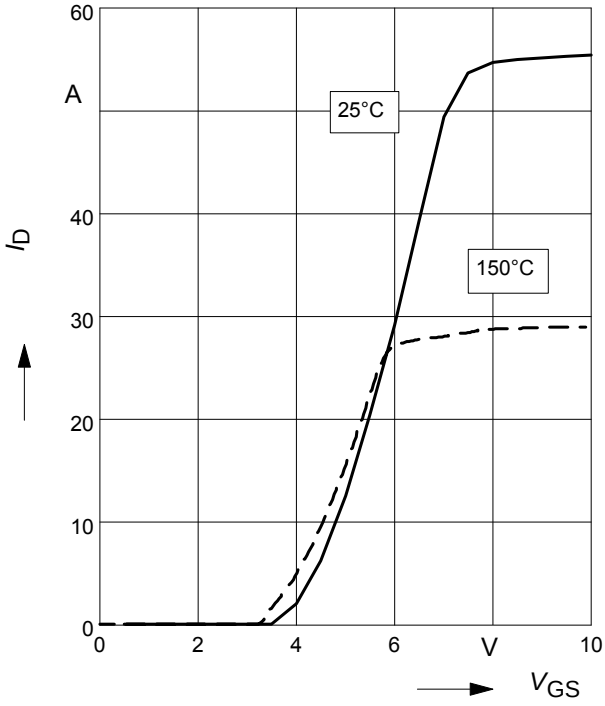
parameter : I_D = 9.4 A, V_{GS} = 10 V



8 Typ. transfer characteristics

$I_D= f(V_{GS})$; $V_{DS}\geq 2 \times I_D \times R_{DS(on)max}$

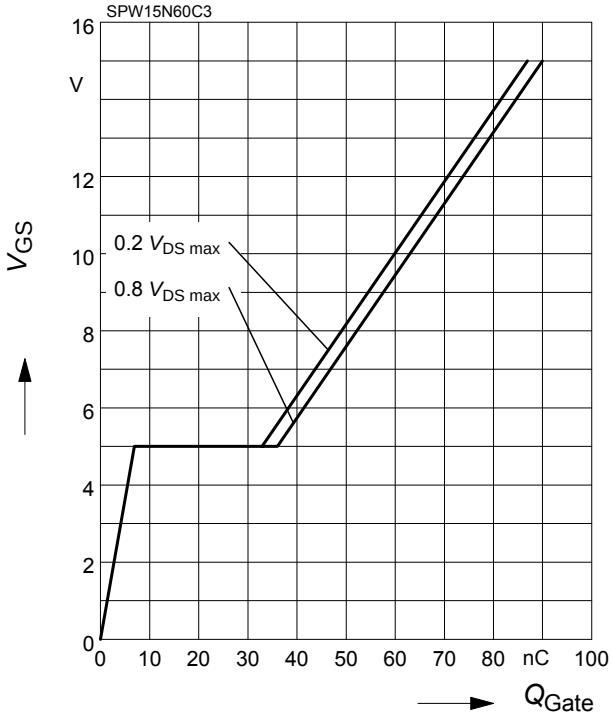
parameter: t_p = 10 µs



9 Typ. gate charge

$V_{GS} = f\ (Q_{Gate})$

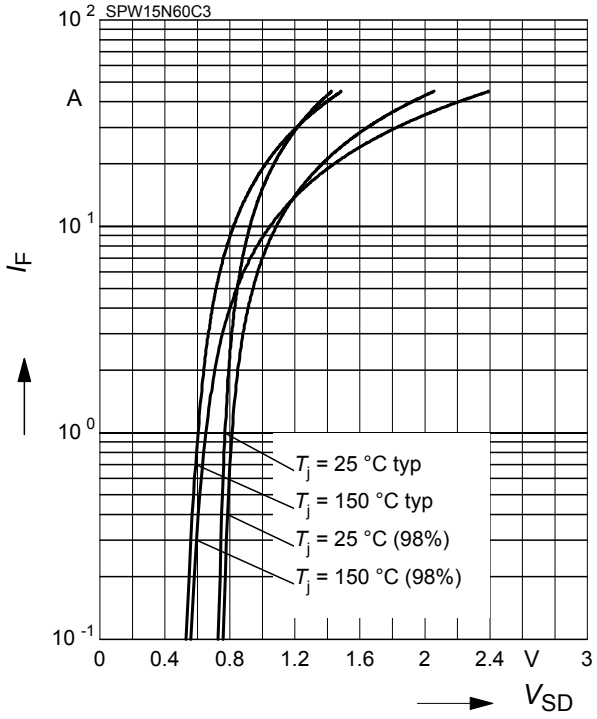
parameter: I_D = 15 A pulsed



10 Forward characteristics of body diode

$I_F = f\ (V_{SD})$

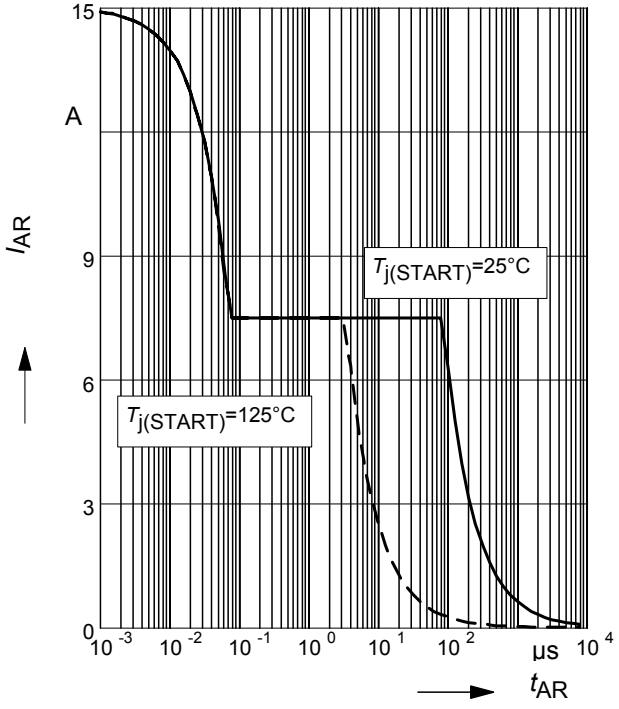
parameter: T_j , tp = 10 µs



11 Avalanche SOA

$I_{AR} = f\ (t_{AR})$

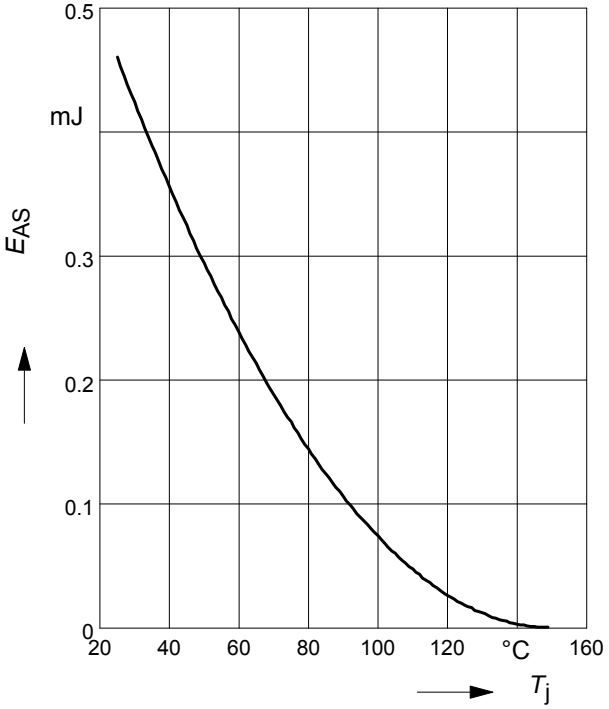
par.: $T_j \leq 150$ °C



12 Avalanche energy

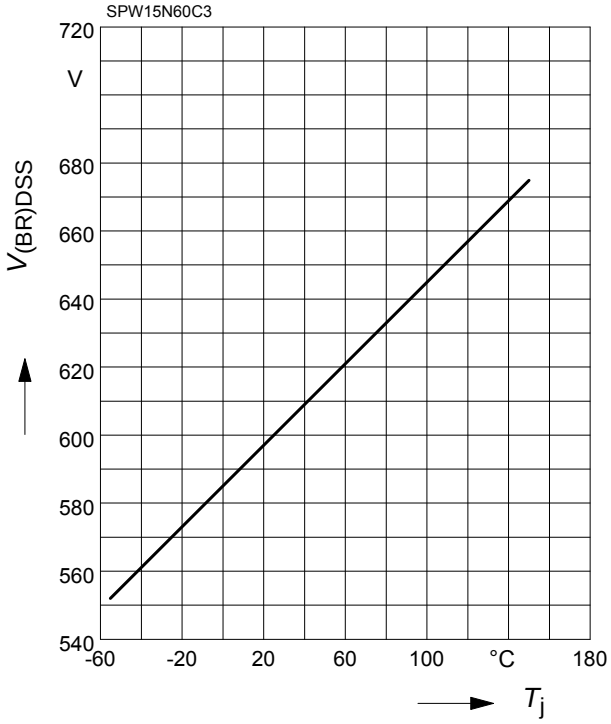
$E_{AS} = f\ (T_j)$

par.: I_D = 7.5 A, V_{DD} = 50 V



13 Drain-source breakdown voltage

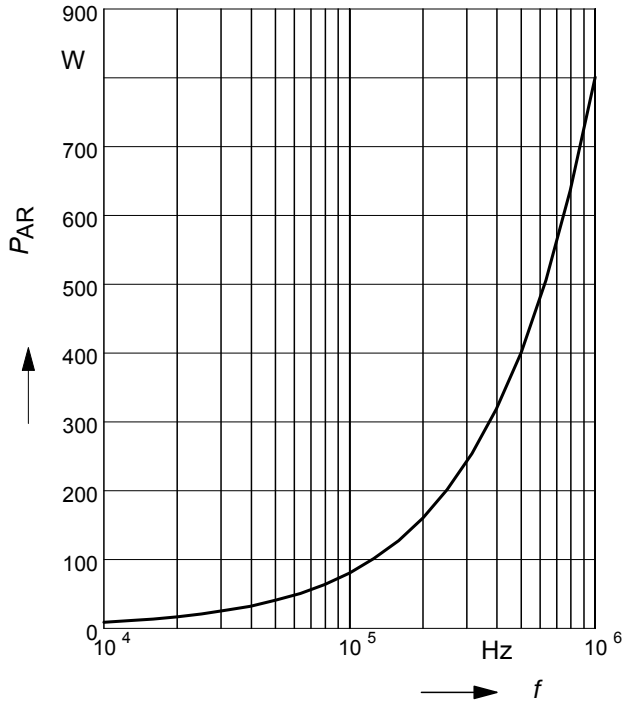
$V_{(BR)DSS} = f(T_j)$



14 Avalanche power losses

$P_{AR} = f(f)$

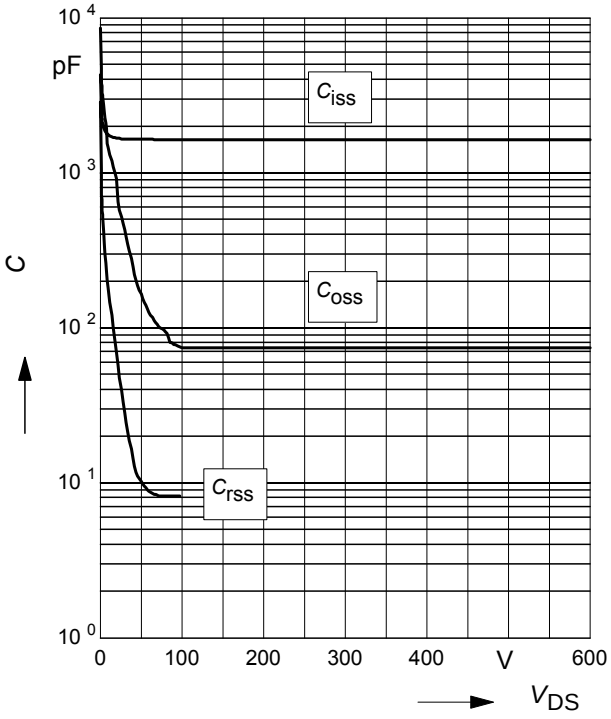
parameter: E_{AR}=0.8mJ



15 Typ. capacitances

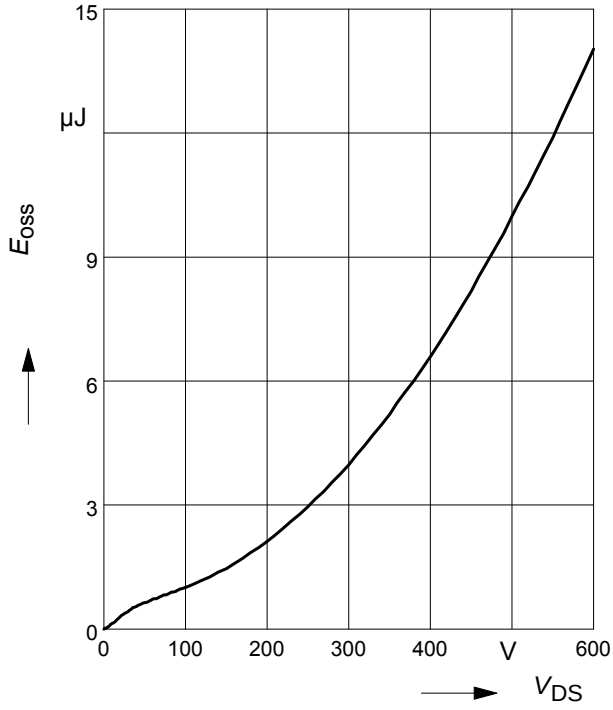
$C = f(V_{DS})$

parameter: V_{GS}=0V, f=1 MHz

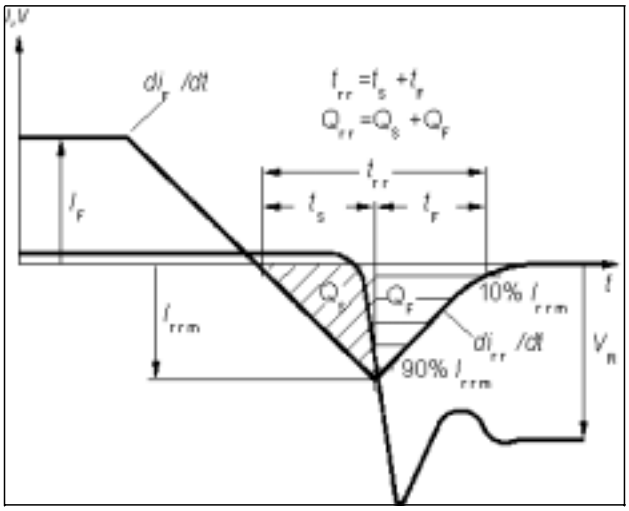


16 Typ. C_{oss} stored energy

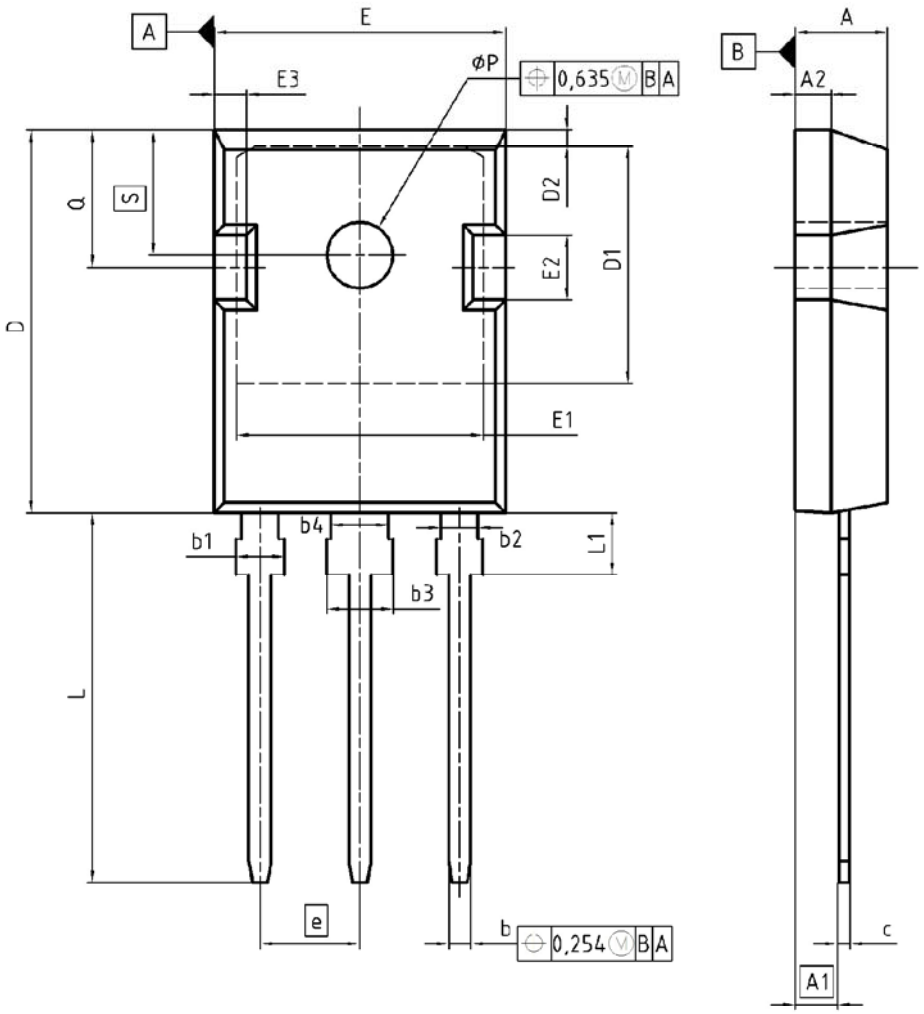
$E_{oss}=f(V_{DS})$



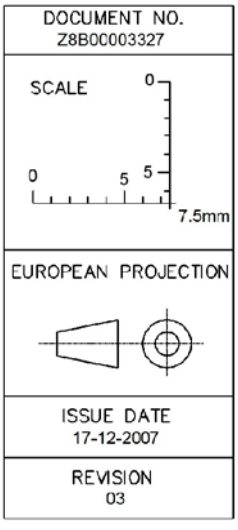
Definition of diodes switching characteristics



PG-TO-247-3-1



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.16	0.193	0.203
A1	2.27	2.53	0.089	0.099
A2	1.85	2.11	0.073	0.083
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.82	21.10	0.820	0.831
D1	16.25	17.65	0.640	0.695
D2	1.05	1.35	0.041	0.053
E	15.70	16.03	0.618	0.631
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.68	2.60	0.066	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.31	0.780	0.799
L1	4.17	4.47	0.164	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248



Please note the new package dimensions arccording to PCN 2009-134-A

Published by
Infineon Technologies AG
81726 Munich, Germany

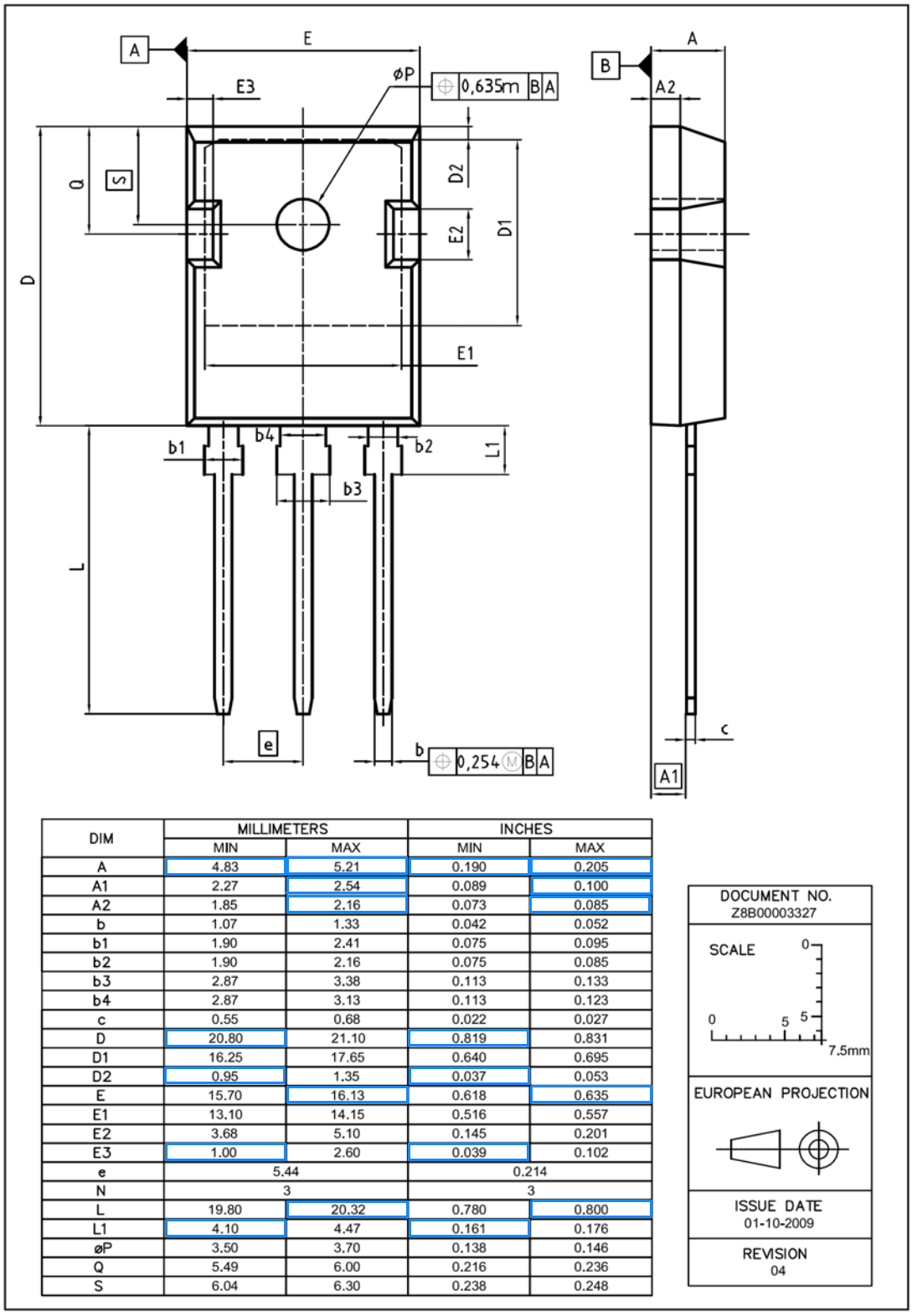
Legal Disclaimer
The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information
For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings
Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

1 New package outlines TO-247

Assembly capacity extension for CoolMOSTM technology products assembled in lead-free package PG-TO247-3 at subcontractor ASE (Weihai) Inc., China (Changes are marked in blue.)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO.
Z8B00003327

SCALE 0 5 5 7.5mm

EUROPEAN PROJECTION

ISSUE DATE
01-10-2009

REVISION
04

Figure 1 Outlines TO-247, dimensions in mm/inches

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Infineon:
SPW15N60C3